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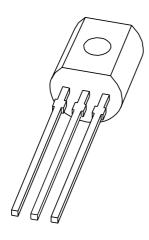






### **DISCRETE SEMICONDUCTORS**

## DATA SHEET



PBSS8110S 100 V, 1 A NPN low V<sub>CEsat</sub> (BISS) transistor

Product data sheet Supersedes data of 2003 Nov 11 2004 Aug 13



## 100 V, 1 A NPN low V<sub>CEsat</sub> (BISS) transistor

### **PBSS8110S**

### **FEATURES**

- SOT54 package
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- $\bullet$  High collector current capability:  $I_{C}$  and  $I_{CM}$
- Higher efficiency leading to less heat generation.

### **APPLICATIONS**

- Automotive 42 V power
- · Telecom infrastructure
- · General industrial applications
- Power management
  - DC/DC converters
  - Supply line switching
  - Battery charger
  - LCD backlighting.
- · Peripheral drivers
  - Generic driver (e.g. lamps and LEDs)
  - Inductive load driver (e.g. relays, buzzers and motors).

### **DESCRIPTION**

NPN low  $V_{\text{CEsat}}$  BISS transistor in a SOT54 plastic package.

### **MARKING**

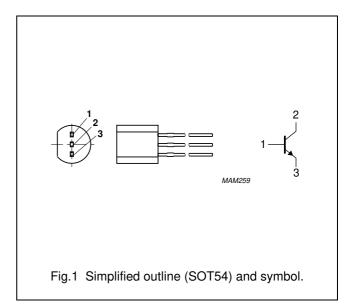
TYPE NUMBER	MARKING CODE
PBSS8110S	S8110S

### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	UNIT
V <sub>CEO</sub>	collector-emitter voltage	100	٧
I <sub>C</sub>	collector current (DC)	1	Α
I <sub>CM</sub>	peak collector current	3	Α
R <sub>CEsat</sub>	equivalent on-resistance	200	mΩ

### **PINNING**

PIN	DESCRIPTION
1	base
2	collector
3	emitter



### **ORDERING INFORMATION**

TYPE NUMBER	PACKAGE				
TTPE NOWIDER	NAME	DESCRIPTION	VERSION		
PBSS8110S	-	plastic single-ended leaded (through hole) package; 3 leads	SOT54		

## 100 V, 1 A NPN low V<sub>CEsat</sub> (BISS) transistor

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### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	_	120	V
$V_{CEO}$	collector-emitter voltage	open base	_	100	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	5	V
I <sub>C</sub>	collector current (DC)		_	1	Α
I <sub>CM</sub>	peak collector current	T <sub>j max</sub>	_	3	Α
I <sub>B</sub>	base current (DC)		_	300	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	_	830	mW
Tj	junction temperature		_	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

### Note

1. Device mounted on a FR4 printed-circuit board; single-sided copper; tinplated; standard footprint.

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	in free air; note 1	150	K/W

### Note

1. Device mounted on a FR4 printed-circuit board; single-sided copper; tinplated; standard footprint.

# 100 V, 1 A NPN low $V_{CEsat}$ (BISS) transistor

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### **CHARACTERISTICS**

 $T_j$  = 25  $^{\circ}C$  unless otherwise specified.

SYMBOL	PARAMETER CONDITIONS		MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector cut-off current	V <sub>CB</sub> = 80 V; I <sub>E</sub> = 0	_	_	100	nA
		V <sub>CB</sub> = 80 V; I <sub>E</sub> = 0; T <sub>j</sub> = 150 °C	_	_	50	μΑ
I <sub>CES</sub>	collector cut-off current	V <sub>CE</sub> = 80 V; V <sub>BE</sub> = 0	_	_	100	nA
I <sub>EBO</sub>	emitter cut-off current	V <sub>EB</sub> = 4 V; I <sub>C</sub> = 0	_	_	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 10 V; I <sub>C</sub> = 1 mA	150	_	_	
		V <sub>CE</sub> = 10 V; I <sub>C</sub> = 250 mA	150	_	500	
		V <sub>CE</sub> = 10 V; I <sub>C</sub> = 0.5 A; note 1	100	_	_	
		V <sub>CE</sub> = 10 V; I <sub>C</sub> = 1 A; note 1	80	_	_	
V <sub>CEsat</sub>	collector-emitter saturation	I <sub>C</sub> = 100 mA; I <sub>B</sub> = 10 mA	_	_	40	mV
	voltage	$I_C = 500 \text{ mA}; I_B = 50 \text{ mA}$	_	_	120	mV
		I <sub>C</sub> = 1 A; I <sub>B</sub> = 100 mA	_	_	200	mV
R <sub>CEsat</sub>	equivalent on-resistance	I <sub>C</sub> = 1 A; I <sub>B</sub> = 100 mA; note 1	_	165	200	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = 1 A; I <sub>B</sub> = 100 mA; note 1	_	_	1.05	V
V <sub>BEon</sub>	base-emitter turn-on voltage	V <sub>CE</sub> = 10 V; I <sub>C</sub> = 1 A	_	_	0.9	V
f <sub>T</sub>	transition frequency	$V_{CE} = 10 \text{ V}; I_{C} = 50 \text{ mA}; f = 100 \text{ MHz}$	100	_	_	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = I_e = 0; f = 1 \text{ MHz}$	_	_	7.5	рF

### Note

1. Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$ 

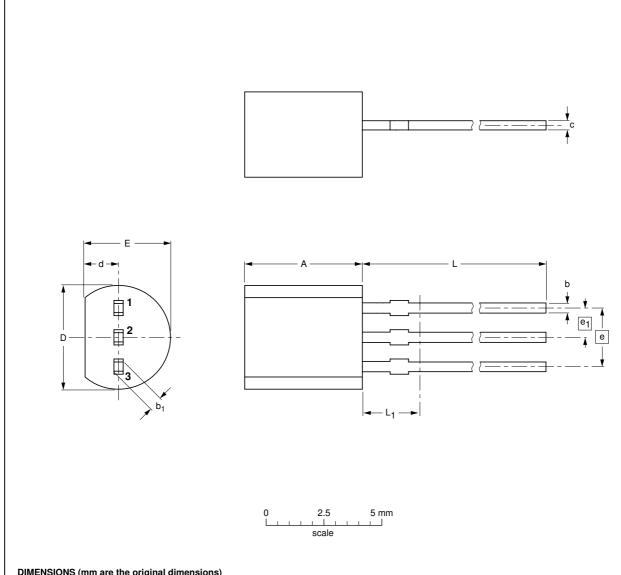
## 100 V, 1 A NPN low V<sub>CEsat</sub> (BISS) transistor

**PBSS8110S** 

### **PACKAGE OUTLINE**

### Plastic single-ended leaded (through hole) package; 3 leads

SOT54



### DIMENSIONS (mm are the original dimensions)

UNIT	A	b	b <sub>1</sub>	С	D	d	E	е	e <sub>1</sub>	L	L <sub>1</sub> <sup>(1)</sup> max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT54		TO-92	SC-43A			<del>-04-06-28</del> 04-11-16	

2004 Aug 13 5

## 100 V, 1 A NPN low V<sub>CEsat</sub> (BISS) transistor

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### **DATA SHEET STATUS**

DOCUMENT STATUS(1)	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

#### **Notes**

- 1. Please consult the most recently issued document before initiating or completing a design.
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### **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

### **Contact information**

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Printed in The Netherlands R75/02/pp7 Date of release: 2004 Aug 13 Document order number: 9397 750 13642

